1. General description

NPN high power bipolar transistor in a power DPAK, TO-252 (SOT428C) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- High thermal power dissipation capability
- High energy efficiency due to less heat generation
- Electrically similar to popular MJD2873 series
- · Low collector emitter saturation voltage
- Fast switching speeds
- · Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Power management
- · Load switch
- Linear mode voltage regulator
- · Constant current drive backlighting application
- Motor drive
- Relay replacement

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	50	V
Ic	collector current		-	-	2	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	3	А
h _{FE}	DC current gain	V_{CE} = 2 V; I_{C} = 0.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	120	-	360	
		V_{CE} = 2 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	40	-	-	



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	mb	
2	С	collector		E
3	Е	emitter		в -[**
mb	С	mounting base; connected to collector	DPAK (SOT428C)	C; mb aaa-029889

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
MJD2873-Q		Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428C			

7. Marking

Table 4. Marking codes

Type number	Marking code
MJD2873-Q	MJD2873A

8. Limiting values

Table 5. Limiting values

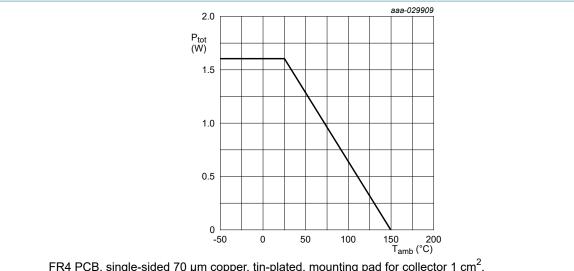
In accordance with the Absolute Maximum Rating System (IEC601134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	50	V
V_{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	2	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	3	Α
P _{tot}	total power dissipation	T _{mb} ≤ 25 °C	[1]	-	15	W
		T _{amb} ≤ 25 °C	[2]	-	1.6	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Total power dissipation junction to mounting base.

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided 70 μm copper, tin-plated mounting pad for collector 1 cm².

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FR4 PCB, single-sided 70 µm copper, tin-plated, mounting pad for collector 1 cm².

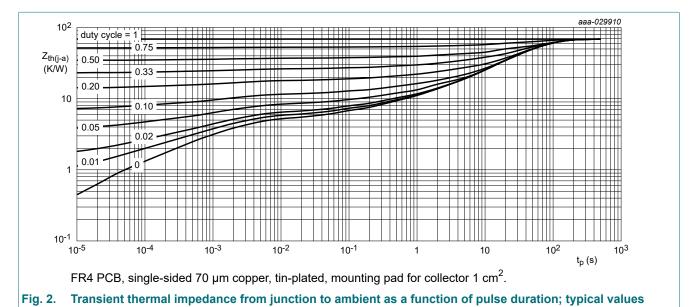
Fig. 1. **Power derating curves SOT428C**

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	79	K/W
R _{th(j-mb)}	thermal resistance from junction to mounting base			-	-	9	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided 70 µm copper, tin-plated mounting pad for collector 1 cm².



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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	N	Vlin	Тур	Max	Unit
I _{CES}	collector-emitter cut-off current	V _{CE} = 50 V; V _{BE} = 0 V; T _{amb} = 25 °C	-		-	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-		-	100	nA
h _{FE}	DC current gain	V_{CE} = 2 V; I_{C} = 0.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	1	120	-	360	
		V_{CE} = 2 V; I_{C} = 2 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	4	10	-	-	
		V_{CE} = 1.6 V; I_{C} = 0.75 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	8	30	-	360	
V _{CEsat}	collector-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	•	-	0.3	V
V _{BEsat}	base-emitter saturation voltage		-	•	-	1.2	V
V_{BE}	base-emitter voltage	V_{CE} = 2 V; I_{C} = 1 A; pulsed; $t_{p} \le 300 \ \mu s$; T_{amb} = 25 °C	-		-	1.2	V
		V_{CE} = 1.6 V; I_{C} = 0.75 A; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	•	-	0.95	V
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-		-	80	pF
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 100 mA; f = 100 MHz; T_{amb} = 25 °C	6	35	-	-	MHz

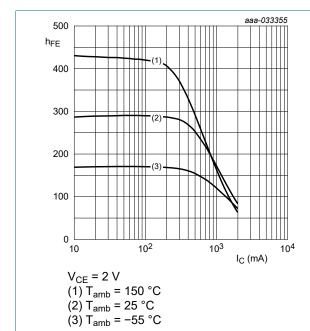


Fig. 3. DC current gain as a function of collector current; typical values

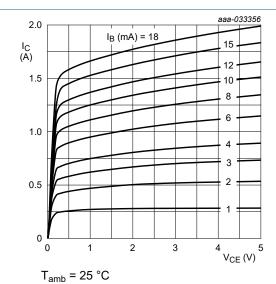
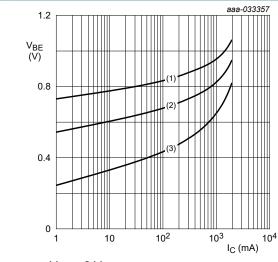


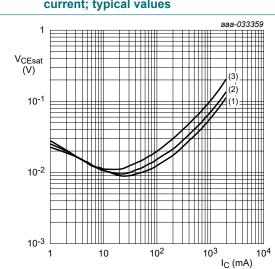
Fig. 4. Collector current as a function of collectoremitter voltage; typical values

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V_{CE} = 2 V (1) T_{amb} = -55 °C (2) T_{amb} = 25 °C (3) T_{amb} = 150 °C

Fig. 5. Base-emitter voltage as a function of collector current; typical values

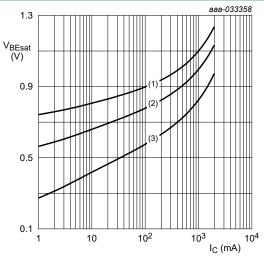


 $I_C/I_B = 20$

(1) $T_{amb} = -55 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$

(3) $T_{amb} = 150 \, ^{\circ}C$

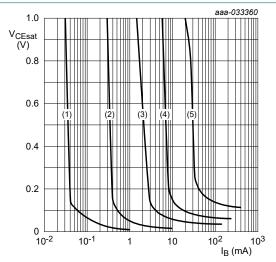
Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



 $I_{C}/I_{B} = 20$ (1) $T_{amb} = -55 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values



 T_{amb} = 25 °C

(1) $I_C = 0.01 A$

(2) $I_C = 0.10 \text{ A}$

 $(3) I_C = 0.50 A$

 $(4) I_C = 1.00 A$

 $(5) I_C = 2.00 A$

Fig. 8. Collector-emitter saturation region as a function of base current; typical values

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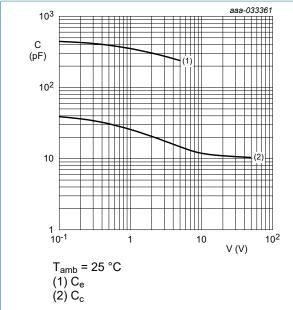


Fig. 9. Input/output capacitance as a function of input/output voltage

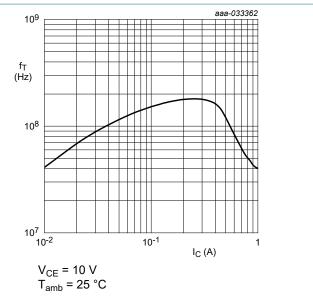


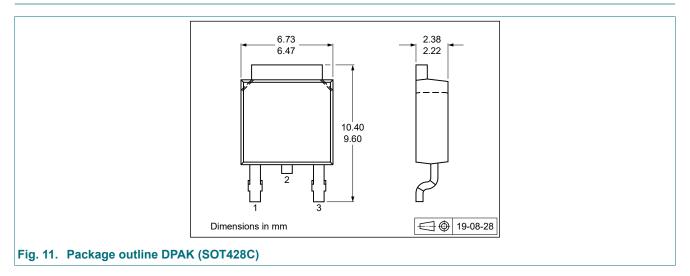
Fig. 10. Transition frequency as a function of collector current; typical values

11. Test information

Quality information

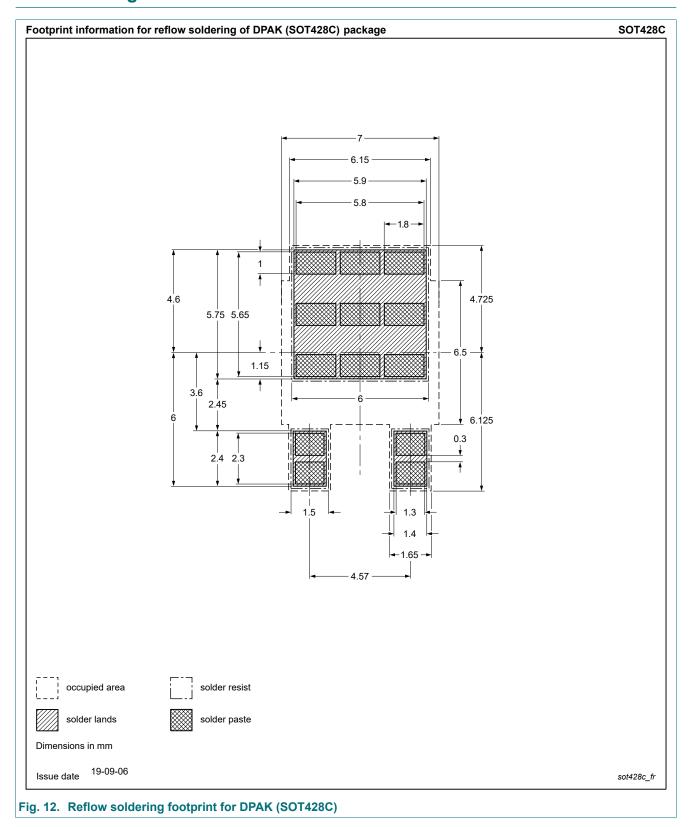
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
MJD2873-Q v.2	20210517	Product data sheet	-	MJD2873-Q v.1			
Modifications:	 Product status 	Product status changed					
MJD2873-Q v.1	20210426	Objective data sheet	-	-			

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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MJD2873-Q

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